

# **isc Silicon NPN Power Transistor**

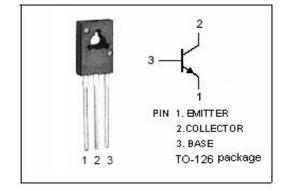
#### **DESCRIPTION**

- Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub> = 150 V(Min)
- DC Current Gain-
  - :  $h_{FE} = 20(Min) @ I_C = 150mA$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



#### **APPLICATIONS**

 Designed for medium voltage and extended range amplifiers applications.



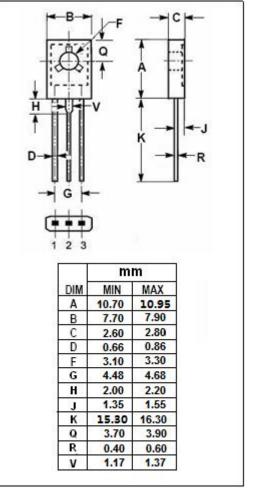
## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	175	V
V <sub>CEO</sub>	Collector-Emitter Voltage	150	V
V <sub>EBO</sub>	Emitter-Base Voltage	3	V
Ic	Collector Current-Continuous	0.5	А
lв	Base Current-Continuous	0.25	А
Pc	Collector Power Dissipation T <sub>C</sub> =25 ℃	20	W
Ti	Junction Temperature 150		$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range -65~1		$^{\circ}$

# THERMAL CHARACTERISTICS

SYMBOL	MBOL PARAMETER		UNIT
R <sub>th j-c</sub>	R <sub>th j-c</sub> Thermal Resistance,Junction to Case		°C/W

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**MJE341** 

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub> =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 1.0mA; I <sub>B</sub> = 0	150		V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 175V; I <sub>E</sub> = 0		0.3	mA
Iceo	Collector Cutoff Current	V <sub>CE</sub> = 150V; I <sub>B</sub> = 0		1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 3V; I <sub>C</sub> = 0		0.1	mA
h <sub>FE -1</sub>	DC Current Gain	I <sub>C</sub> = 10m A; V <sub>CE</sub> = 10V	20		
h <sub>FE</sub> -2	DC Current Gain	I <sub>C</sub> = 50m A; V <sub>CE</sub> = 10V	25	200	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 150m A; V <sub>CE</sub> = 10V	20		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 150mA ;I <sub>B</sub> = 15mA		2.3	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 50mA; V <sub>CE</sub> = 10V		1.0	V
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 50m A; V <sub>CE</sub> = 25V;	15		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 20V,f <sub>test</sub> = 100kHz	15		pF

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